

U.S. Application Serial No.: 10/655,584  
Amendment Dated May 24, 2005  
In Response to Office Action Dated February 25, 2005

**REMARKS**

Claims 1-48 are in this application.

Claims 1-40 and 44 have been canceled.

Claims 41-43 and 45-48 are currently pending in this application.

Claim 41 has been amended.

Claims 41-48 have been rejected under 35 U.S.C. 102(b), as being anticipated by U.S. Patent Application Publication US 2001/0045651 A1 by Saito et al., herein after "Saito et al."

Applicants have canceled claim 44. Therefore, the rejection of claim 44 is moot.

The Office Action refers to the structure described by Saito et al. as having:

"an SiO porous or dense low k dielectric layer 29 (thus selected from the group consisting of: silicon-containing material formed from one or more of Si, C, O, F and H..."

Applicants have amended claim 41 by incorporating a portion of the canceled claim 44 into claim 41. Canceled claim 44 recites:

"44. The interconnect structure of Claim 41, wherein said porous or dense low k dielectric is selected from the group consisting of:

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silicon-containing material formed from one or more of Si, C, O, F and H, PE CVD materials having a composition Si, C, O, and H, a fluorosilicate glass (FSG), C doped oxide, F doped oxide and alloys of Si, C, O and H."

The portion of the canceled claim 44 that was incorporated by the Applicants into claim 41 is:

"wherein said porous or dense low k dielectric is selected from the group consisting of: PE CVD materials having a composition Si, C, O, and H, a fluorosilicate glass (FSG), C doped oxide, F doped oxide and alloys of Si, C, O and H."

Support for the amendment is found in the canceled claim 44 and on page 11, lines 5-20, of the specification, which states:

"Suitable dielectrics for layer 30 are porous or dense inorganic materials including, but not limited to, silicon-containing materials such as compositions formed from one or more of Si, C, O, F and H, e.g., FSG, C doped oxide, F doped oxide, alloys of Si, C, O and H and the like. Specific examples of PE CVD materials of the composition Si, C, O, and H include, but are not limited to, Black Diamond from Applied Materials, Coral from Novellus Systems and Aurora from ASM., all have k approximately 3.0, and include the range 2.8 to 3.2. Also, SiCOH dielectrics containing porosity and having k from 2.7 down to 1.8 may be preferably used within this invention, including BDII and BDIII from Applied Materials, Aurora ULK and ELK from ASM, and other porous SiCOH films. A variety of spin applied films having the composition Si, C, O, H, such as, methylsilsesquioxanes, siloxanes and 5109, 5117, 5525, 5530 from Japan Synthetic Rubber (JSR), and Dendriglass may also be used. The materials known as Orion and other materials from Trikon may also be used."

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Claim 41, as amended, does not recite SiO. Saito et al. does not teach or suggest anywhere that porous or dense low k dielectric material can be "PE CVD materials having a composition Si, C, O, and H, a fluorosilicate glass (FSG), C doped oxide, F doped oxide and alloys of Si, C, O and H."

Therefore, claim 41, as amended, and the claims depending therefrom, are not anticipated by Saito et al.

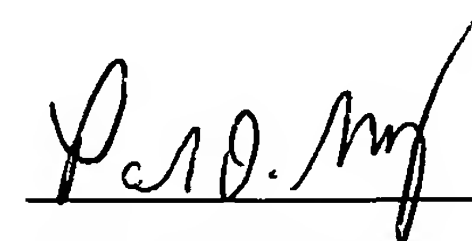
Accordingly, the rejection of claims 41-43 and 45-48 under 35 U.S.C. 102(b), as being anticipated by Saito et al. should be withdrawn and claims 41-43 and 45-48 should be allowed.

Based on the foregoing, currently pending claims, namely claims 41-43 and 45-48, are patentable over the cited art for at least the reasons set forth herein above. Accordingly, reconsideration, withdrawal of the rejection under 35 U.S.C. 102(b), as being anticipated by Saito et al. and allowance of claims 41-48 are respectfully requested.

Respectfully submitted,

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